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## U.S. Patent Documents

#### Foreign Patent Documents

Other Documents (Including Author, Title, Date Pertinent Pages, Etc.)

		Norio Onojima et al., "High-Quality AlN by Initial Layer-by-Layer Growth on Surface-Controlled 4H-SiC(0001) Substrate", <i>Jpn. J. Appl. Phys.</i> Vol. 42, Part 2, No. 5A (May 1, 2003), pp. L445-L447.
		N. Onojima et al., "Impact of SiC Surface Control on Initial Growth Mode and Crystalline Quality of AlN Grown by Molecular-Beam Epitaxy", <i>Phys. Stat. Sol. (c)</i> 0, No. 7 (2003), pp. 2529-2532/DOI 10.1002/pssc.200303358.
		Jun Suda et al., "Either Step-Flow or Layer-by-Layer Growth for AlN on SiC (0001) Substrates", <i>Mat. Res. Soc. Symp. Proc.</i> , Vol. 798 (2004), © Materials Research Society, pp. Y3.4.1-Y3.4.6.
EXAMINER	/Matthew Song/	DATE CONSIDERED
		09/14/2008

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